

# Atomic Layer Deposition Niobium Nitride Films for High-Q Resonators

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## Atomic Layer Deposition

One Plasma-Enhanced Atomic Layer Deposition cycle consists of treating the substrate with the precursor, TBTDEN, removing the precursor from the chamber, lighting the plasma with P = 300W, waiting, turning off the Argon plasma, and removing the excess Ar from the chamber. Furthermore, since Nb has a low vapor pressure, we use three Ar boost cycles to improve chamber precursor concentration. One ALD cycle creates approximately one atomic monolayer of metal, and we repeat this process for a given cycle count to achieve the desired thickness.

## Crystallographic Structure



### Fabrication

Process Step	Machine	Notes
Deposition	Ultratech Fiji Plasma Enhanced Atomic Layer Deposition	Tempera 100 cycl
Lithography	Heidelberg MLA150 Maskless Aligner	Defoc: 0 Dose:12 375nm l
Etch	PlasmaTherm Inductively Coupled Plasma Chlorine Etcher	Etch tim CF <sub>4</sub> Flow CHF <sub>3</sub> Flo Ar Flow:

# RF Characterization

To measure the microwave properties of the ALD NbN films, we construct single-layer microwave resonators and test them to obtain the RF critical temperature  $T_c^{(RF)}$  and quality factor Q. This is done with a simple fabrication process described on the bottom left.



To find  $T_{c}^{(RF)}$ , we measure the frequency shift as a function of stage temperature, and fit to Mattis-Bardeen curves and extrapolate Tc. A sample resonator fit is shown above.



We find all Q values above  $10^4$ , with most above  $10^{-5}$  and many above 10^6. The quality factor performance is maintained as the deposition temperature changes.

ature: 250-300 C les≈6 nm

 $25 \text{ mJ/cm}^2$ laser ne: 5-10 min v: 40 sccm ow: 10 sccm 10 sccm





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# DC T<sub>c</sub> and Thickness

### Acknowledgements

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